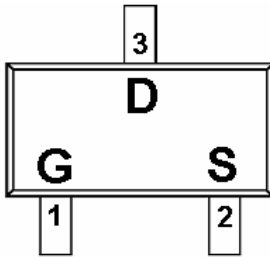
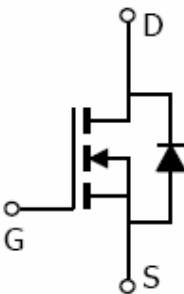
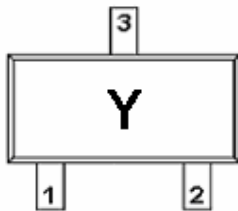


**DESCRIPTION**

STP1013 is the P-Channel enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where high-side switching, low in-line power loss, and resistance to transients are needed.

**PIN CONFIGURATION**  
**SOT-523 / SC-89**

**FEATURE**

- 20V/0.45A,  $R_{DS(ON)} = 520\text{ohm}@V_{GS} = 4.5V$
- 20V/0.35A,  $R_{DS(ON)} = 700\text{ohm}@V_{GS} = 2.5V$
- 20V/0.25A,  $R_{DS(ON)} = 950\text{ohm}@V_{GS} = 1.8V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional low on-resistance and maximum DC current capability
- SOT-523 / SC89 package design

**PART MARKING**


STANSON TECHNOLOGY  
 120 Bentley Square, Mountain View, Ca 94040 USA  
<http://www.stansontech.com>



**STP1013** 

Dual P Channel Enhancement Mode MOSFET  
-0.45A

**ABSOLUTE MAXIMUM RATINGS** (Ta = 25°C Unless otherwise noted )

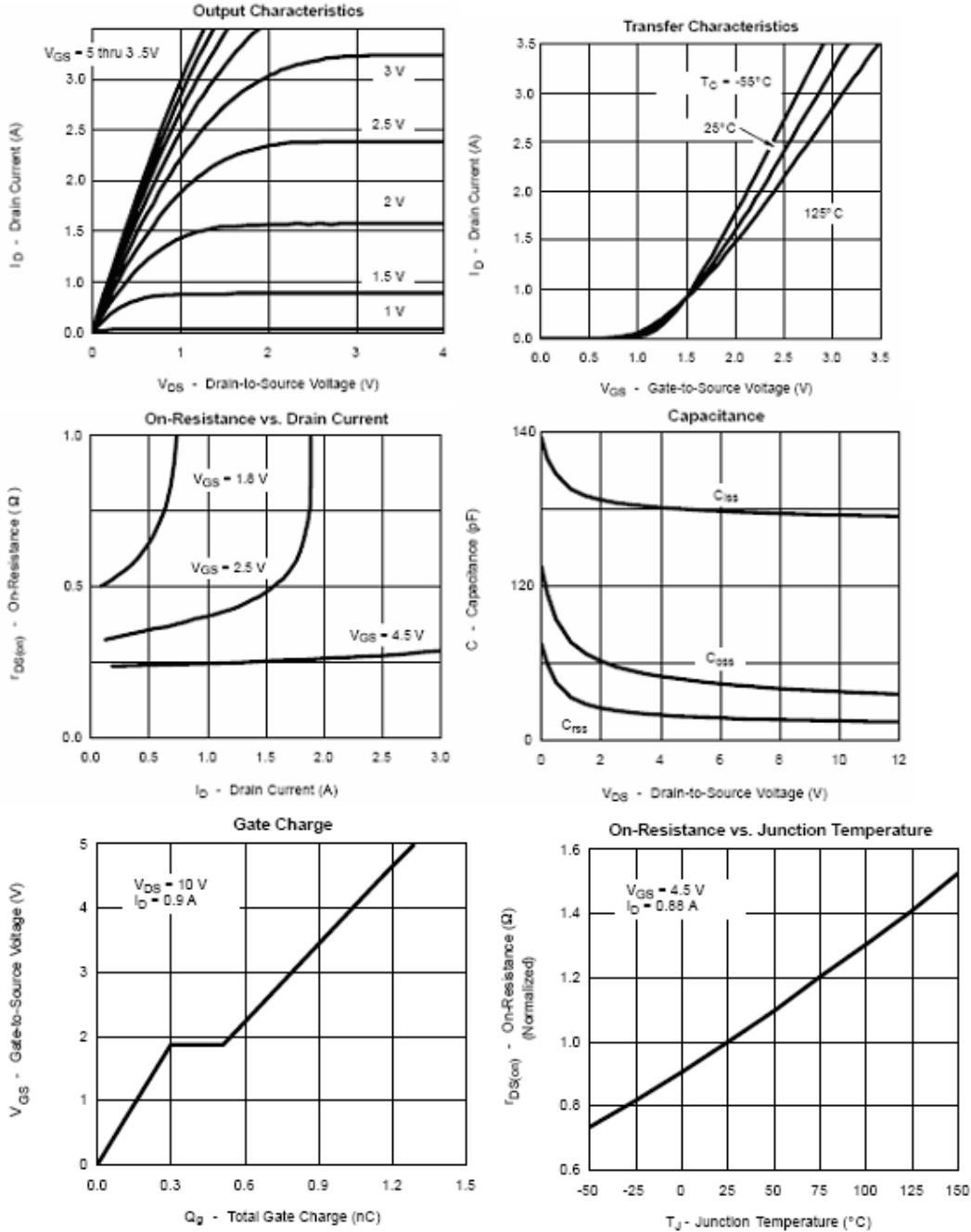
Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-20	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Continuous Drain Current (T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	-0.45
		T <sub>A</sub> =80°C	-0.35
Unit			A
Pulsed Drain Current	I <sub>DM</sub>	-1.0	A
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	-0.3	A
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	0.27
		T <sub>A</sub> =70°C	0.16
Unit			W
Operation Junction Temperature	T <sub>J</sub>	-55/150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C

STANSON TECHNOLOGY  
120 Bentley Square, Mountain View, Ca 94040 USA  
<http://www.stansontech.com>

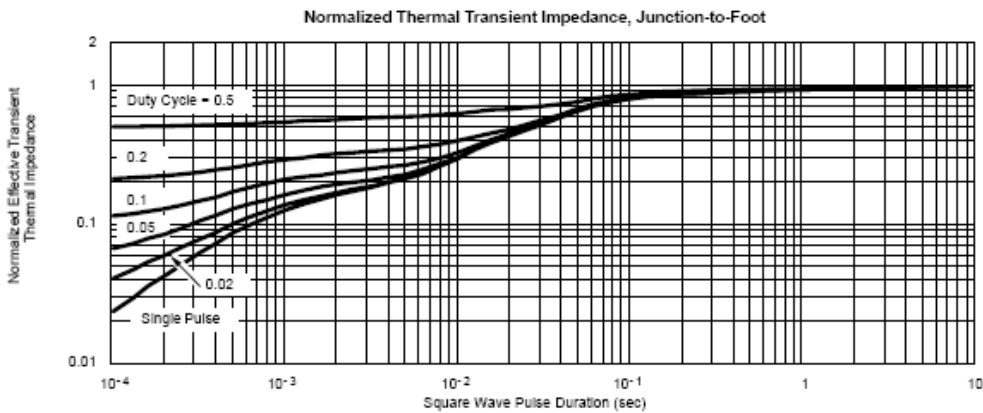
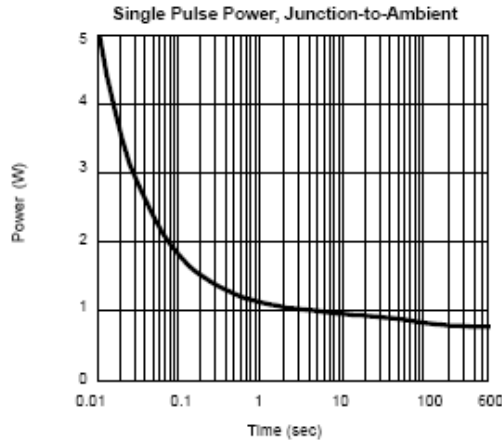
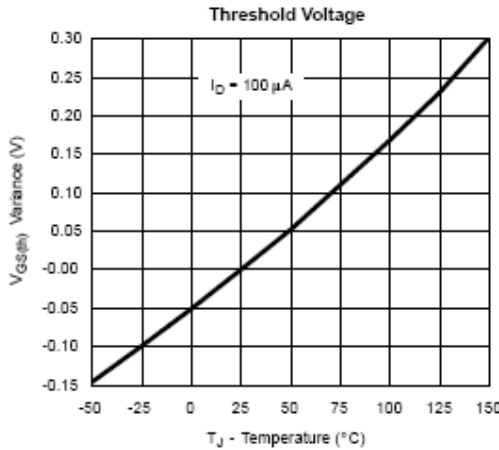
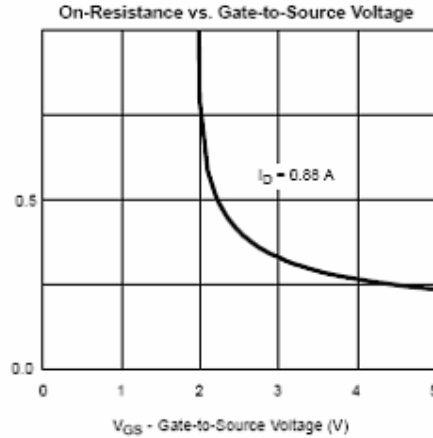
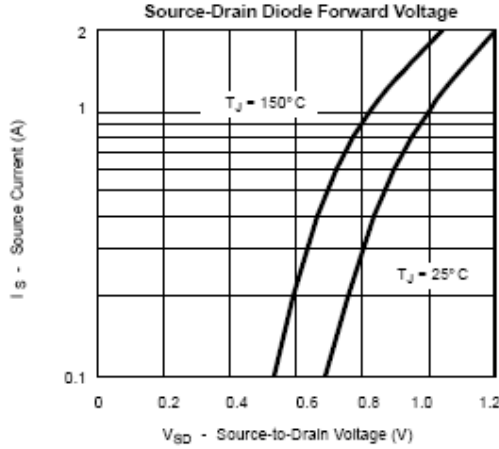
STP1013 2009. V1

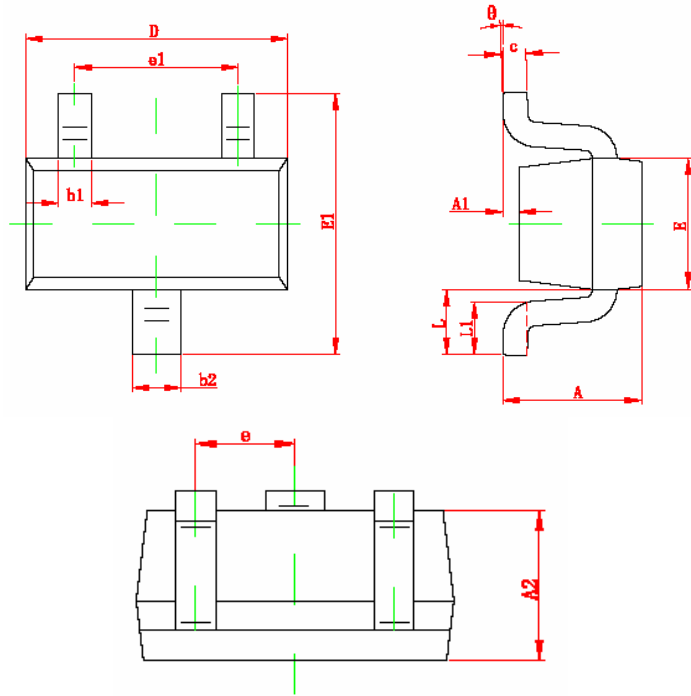
**ELECTRICAL CHARACTERISTICS** ( Ta = 25°C Unless otherwise noted )

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	-0.35		-0.8	V
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 12V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20V, V_{GS}=0V$			-1	uA
		$V_{DS}=20V, V_{GS}=0V$ $T_J=55^\circ C$			-5	
On-State Drain Current	$I_{D(on)}$	$V_{DS}\leq -4.5V, V_{GS}=-5V$	-0.7			A
Drain-source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-0.45A$		420	520	mΩ
		$V_{GS}=-2.5V, I_D=-0.35A$		580	700	
		$V_{GS}=-1.8V, I_D=-0.25A$		750	950	
Forward Transconductance	$g_{fs}$	$V_{DS}=-10V, I_D=-0.25A$		0.4		S
Diode Forward Voltage	$V_{SD}$	$I_S=-0.15A, V_{GS}=0V$		-0.8	-1.2	V
<b>DYNAMIC</b>						
Total Gate Charge	$Q_g$	$V_{DS}=-10V, V_{GS}=-4.5V,$ $V_{DS}=-0.6A$		1.5	2.0	nC
Gate-Source Charge	$Q_{gs}$			0.3		
Gate-Drain Charge	$Q_{gd}$			0.35		
Turn-On Time	$T_{d(on)}$	$V_{DD}=-10V, R_L=10\Omega, I_D=-0.4A,$ $V_{GEN}=-4.5V, R_G=6\Omega$		5	10	nS
	$t_r$			15	25	
Turn-Off Time	$T_{d(off)}$			8	15	
	$t_f$			1.4	1.8	

**TYPICAL CHARACTERISTICS**


**TYPICAL CHARACTERISTICS**



**SOT523 (SC-89) PACKAGE OUTLINE**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.325	0.010	0.013
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.750	0.850	0.030	0.033
E1	1.450	1.750	0.057	0.069
e	0.500 TYP		0.020 TYP	
e1	0.900	1.100	0.035	0.043
L	0.550 REF		0.022 REF	
L1	0.280	0.440	0.011	0.017
$\theta$	0°	4°	0°	4°



**STP1013**   
Lead-free

Dual P Channel Enhancement Mode MOSFET  
-0.45A

---

STANSON TECHNOLOGY  
120 Bentley Square, Mountain View, Ca 94040 USA  
<http://www.stansontech.com>

*STP1013 2009. V1*